

Power logic 8-bit shift register

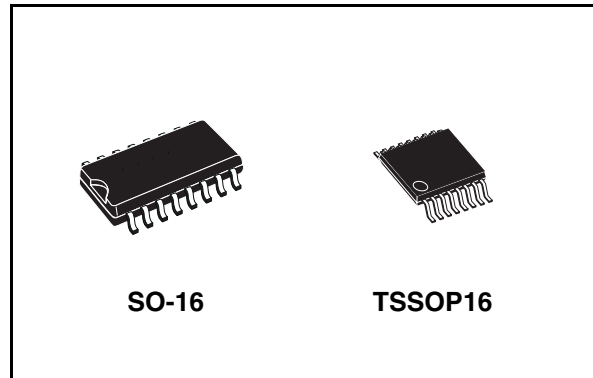
Features

- Low $R_{DS(on)}$: 4 Ω typ
- 30 mJ avalanche energy
- Eight 100 mA DMOS outputs
- 250 mA current limit capability
- 33 V output clamp voltage
- Device are cascadable
- Low power consumption

Description

This STPIC6C595 is a monolithic, medium-voltage, low current power 8-bit shift register designed for use in systems that require relatively moderate load power such as LEDs. The device contains a built-in voltage clamp on the outputs for inductive transient protection. Power driver applications include relays, solenoids, and other low-current or medium-voltage loads.

The device contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. Data transfers through both the shift and storage register clock (SRCK) and the register clock (\overline{RCK}), respectively. The device transfers data out the serial output (SER OUT) port on the rising edge of SRCK. The storage register transfers data to the output buffer when shift register clear (CLR) is high. When \overline{CLR} is low, the input shift register is cleared. When output enable (\overline{G}) is held high, all data in the output buffer is held low and all drain output are off. When G is held low, data from the storage register is transparent to the output buffer.



When data in the output buffers is low, the DMOS transistor outputs are off. When data is high, the DMOS transistor outputs have sink-current capability. The SER OUT allows for cascading of the data from the shift register to additional devices.

Output are low-side, open-drain DMOS transistors with output ratings of 33 V and 100 mA continuous sink-current capability. Each output provides a 250 mA maximum current limit at $T_C = 25\text{ }^\circ\text{C}$. The current limit decreases as the junction temperature increases for additional device protection. The device also provides up to 1.5 kV of ESD protection when tested using the human-body model and 150 V machine model.

The STPIC6C595 is characterized for operation over the operating case temperature range of $-40\text{ }^\circ\text{C}$ to $125\text{ }^\circ\text{C}$.

Table 1. Device summary

Order codes	Package	Packaging
STPIC6C595MTR	SO-16 (Tape and reel)	2500 parts per reel
STPIC6C595TTR	TSSOP16 (Tape and reel)	2500 parts per reel

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1 Logic symbol and pin configuration

Figure 1. Logic symbol and pin configuration

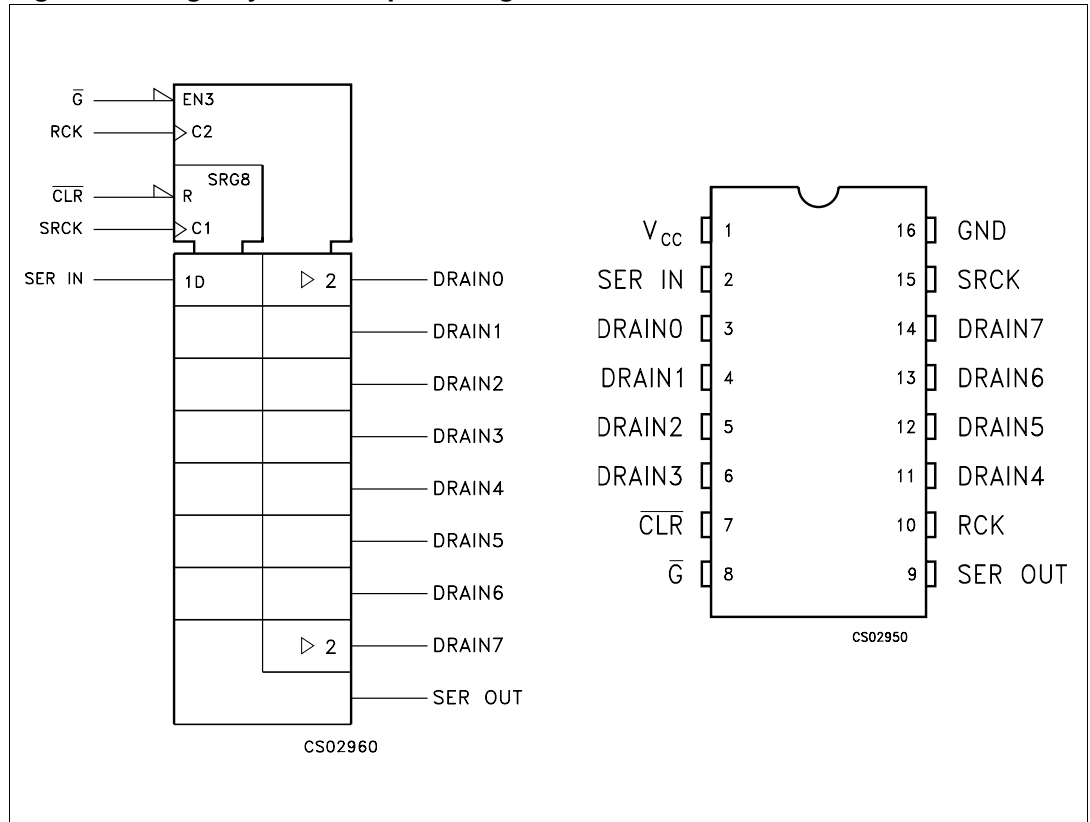
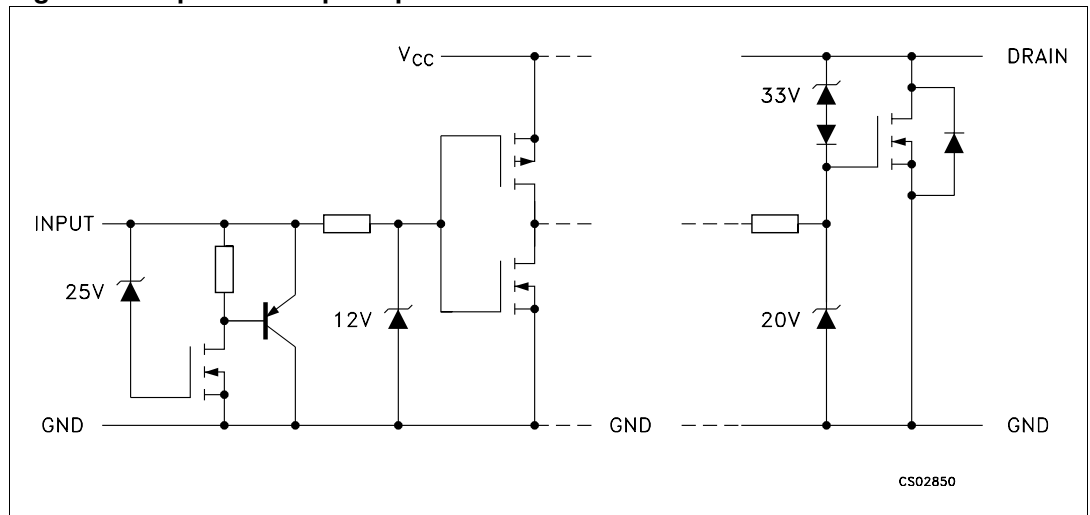


Figure 2. Input and output equivalent circuits



2 Maximum rating

Stressing the device above the rating listed in the “absolute maximum ratings” table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2.1 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	Logic supply voltage (See Note 1)	7	V
V_I	Logic input voltage range	-0.3 to 7	V
V_{DS}	Power DMOS drain to source voltage (See Note 2)	33	V
I_{DS}	Continuous source to drain diode anode current	250	mA
I_{DS}	Pulsed source to drain diode anode current (See Note 3)	500	mA
I_D	Pulsed drain current, each output, all output ON ($T_C = 25\text{ °C}$)	250	mA
I_D	Continuous current, each output, all output ON ($T_C = 25\text{ °C}$)	100	mA
I_D	Peak drain current single output ($T_C = 25\text{ °C}$) (See Note 3)	250	mA
E_{AS}	Single pulse avalanche energy (See Figure 11 and Figure 12)	30	mJ
I_{AS}	Avalanche current (See Note 4 and Figure 17)	200	mA
P_d	Continuous total dissipation ($T_C \leq 25\text{ °C}$)	1087	mW
P_d	Continuous total dissipation ($T_C = 125\text{ °C}$)	217	mW
T_J	Operating virtual junction temperature range	-40 to +150	°C
T_C	Operating case temperature range	-40 to +125	°C
T_{stg}	Storage temperature range	-65 to +150	°C
T_L	Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds	260	°C

2.2 Thermal data

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{th(JA)}$	Thermal resistance junction-ambient	115	°C/W

2.3 Recommended operating conditions

Table 4. Recommended operating conditions

Symbol	Parameter	Min	Typ	Max	Unit
V_{CC}	Logic supply voltage	4.5		5.5	V
V_{IH}	High level input voltage	$0.85V_{CC}$		V_{CC}	V
V_{IL}	Low level input voltage	0		$0.15V_{CC}$	V
I_{DP}	Pulse drain output current ($T_C = 25\text{ °C}$, $V_{CC} = 5\text{ V}$, all outputs ON) (see Note 3 , Note 5 and Figure 15)			250	mA
t_{su}	Set-up time, SER IN high before SRCK \uparrow (see Figure 4 and Figure 8)	1.6	3.0	5.7	ns
t_{hL}	Hold time, SER IN high before \bar{G} \uparrow (see Figure 4 , Figure 7 , Figure 8)	2.8	4.0	9.6	ns
t_W	Pulse duration (see Figure 8)	40			ns
T_C	Operating case temperature	-40		125	°C

3 Electrical characteristics

3.1 DC characteristics

Table 5. DC characteristics ($V_{CC} = 5\text{ V}$, $T_C = 25\text{ °C}$, unless otherwise specified.)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$V_{(BR)DSX}$	Drain-to-source breakdown voltage	$I_D = 1\text{ mA}$	33	37		V
V_{SD}	Source-to-drain diode forward voltage	$I_F = 100\text{ mA}$		0.85	1.2	V
V_{OH}	High level output voltage SER OUT	$I_{OH} = -20\text{ }\mu\text{A}$, $V_{CC} = 4.5\text{ V}$	4.4	4.49		V
		$I_{OH} = -4\text{ mA}$, $V_{CC} = 4.5\text{ V}$	4	4.2		V
V_{OL}	Low level output voltage SER OUT	$I_{OH} = 20\text{ }\mu\text{A}$, $V_{CC} = 4.5\text{ V}$		0.005	0.1	V
		$I_{OH} = 4\text{ mA}$, $V_{CC} = 4.5\text{ V}$		0.3	0.5	V
I_{IH}	High level input current	$V_{CC} = 5.5\text{ V}$, $V_I = V_{CC}$			1	μA
I_{IL}	Low level input current	$V_{CC} = 5.5\text{ V}$, $V_I = 0$			-1	μA
I_{CC}	Logic supply current	$V_{CC} = 5.5\text{ V}$, all outputs OFF or ON		20	200	μA
$I_{CC(FRQ)}$	Logic supply current at frequency	$f_{SRCK} = 5\text{ MHz}$, $C_L = 30\text{ pF}$ All outputs OFF (See Figure 6 , Figure 18 and Figure 19)		0.2	2	mA
I_N	Nominal current	$V_{DS(on)} = 0.5 V$, $I_N = I_D$ $T_C = 85\text{ °C}$ (See Note 5 , Note 6 , Note 7)		90		mA
I_{DSX}	Off-state drain current	$V_{DS} = 30\text{ V}$, $V_{CC} = 5.5\text{ V}$		0.3	5	μA
		$V_{DS} = 30\text{ V}$, $V_{CC} = 5.5\text{ V}$ or 0 V $T_C = 125\text{ °C}$		0.6	8	μA
$R_{DS(on)}$	Static drain source on state resistance (See Note 5 , Note 6 and Figure 14 , Figure 16)	$I_D = 50\text{ mA}$, $V_{CC} = 4.5\text{ V}$		4.5	6	Ω
		$I_D = 50\text{ mA}$, $V_{CC} = 4.5\text{ V}$ $T_C = 125\text{ °C}$		6.5	9	Ω
		$I_D = 100\text{ mA}$, $V_{CC} = 4.5\text{ V}$		4.5	6	Ω

3.2 Switching characteristics

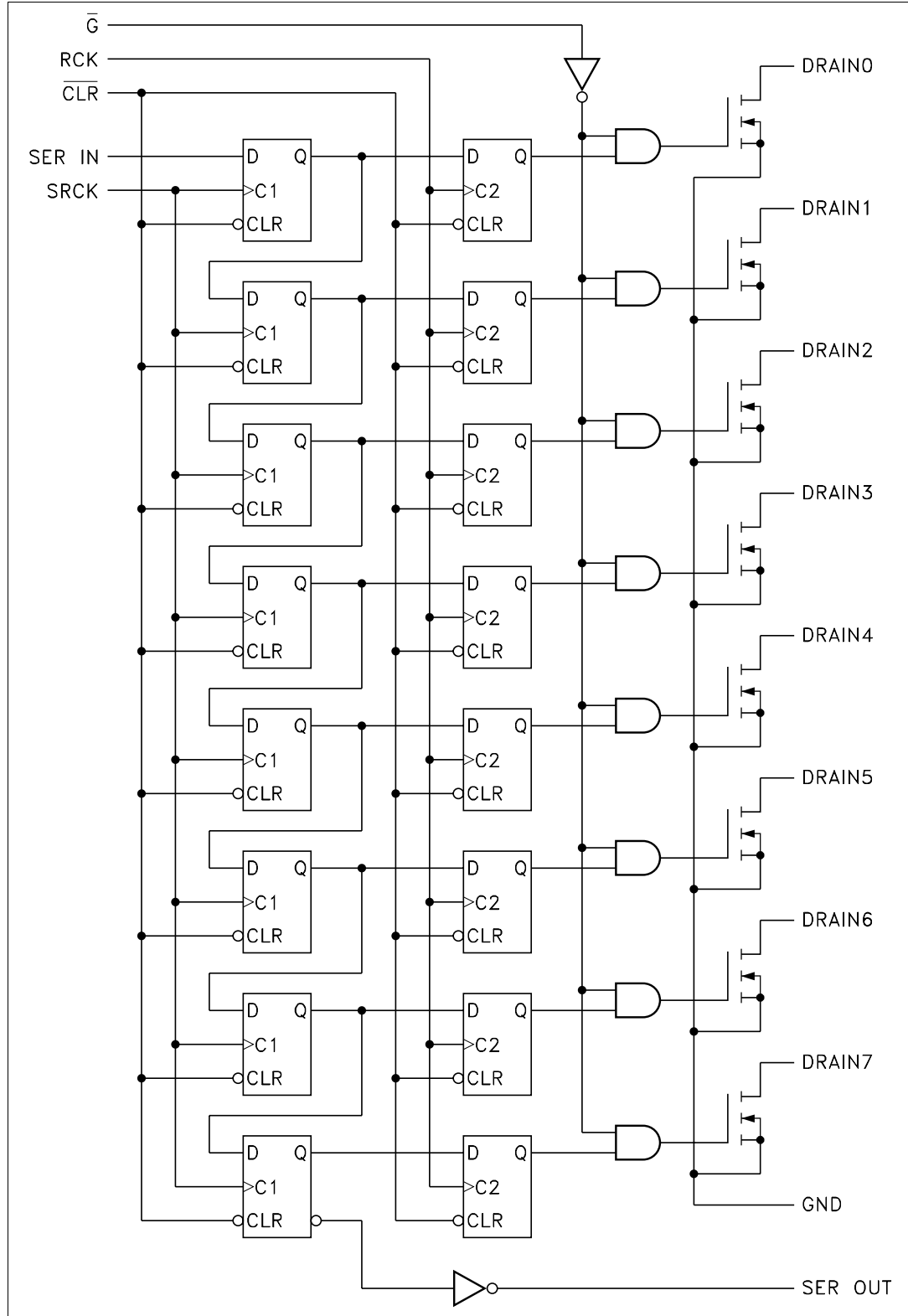
Table 6. Switching characteristics ($V_{CC} = 5\text{ V}$, $T_C = 25\text{ °C}$, unless otherwise specified.)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
t_{PHL}	Propagation delay time, high to low level output from \overline{G}	$C_L = 30\text{ pF}$, $I_D = 75\text{ mA}$ (See Figure 4 , Figure 5 , Figure 6 , Figure 7 , Figure 20)		80		ns
t_{PLH}	Propagation delay time, low to high level output from \overline{G}			130		ns
t_r	Rise time, drain output			60		ns
t_f	Fall time, drain output			50		ns
t_{pd}	propagation delay time			20		ns
t_a	Reverse recovery current rise time	$I_F = 100\text{ mA}$, $di/dt = 10\text{ A}/\mu\text{s}$ (See Figure 5 , Figure 6 , and Figure 9 , Figure 10)		39		ns
t_{rr}	Reverse recovery time			115		ns

- Note:
- 1 All voltage value are with respect to GND
 - 2 Each power DMOS source is internally connected to GND
 - 3 Pulse duration $\leq 100\text{ }\mu\text{s}$ and duty cycle $\leq 2\%$
 - 4 Drain supply voltage = 15 V, starting junction temperature (T_{JS}) = 25 °C. $L = 1.5\text{ H}$ and $I_{AS} = 200\text{ mA}$ (see Fig. 11 and 12)
 - 5 Technique should limit $T_J - T_C$ to 10 °C maximum
 - 6 These parameters are measured with voltage sensing contacts separate from the current-carrying contacts.
 - 7 Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at $T_C = 85\text{ °C}$.

4 Logic diagram

Figure 3. Logic diagram



5 Typical operating circuit

Figure 4. Typical operation mode test circuits

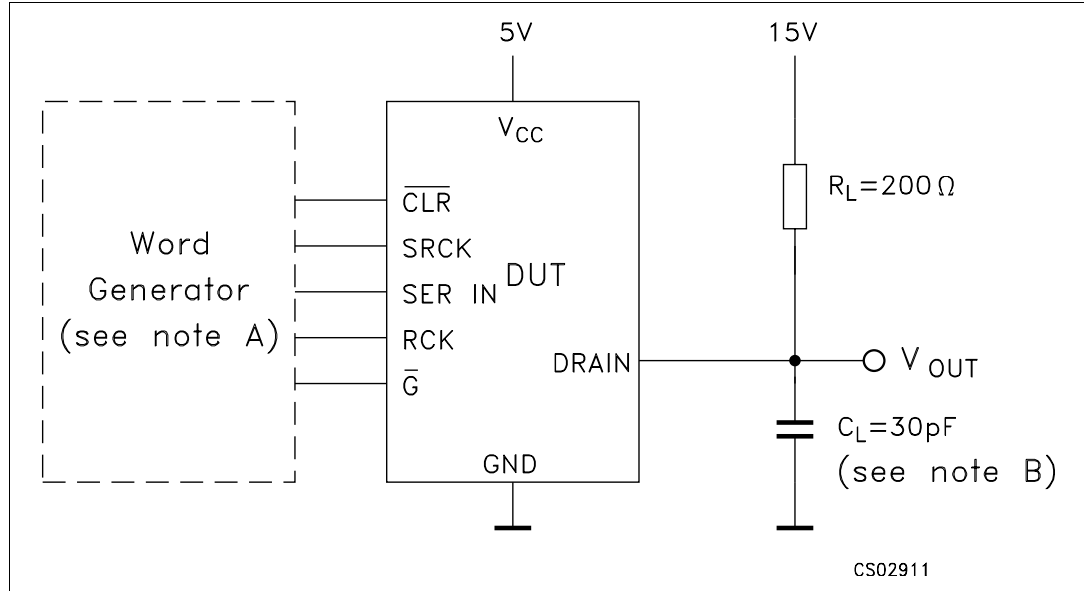
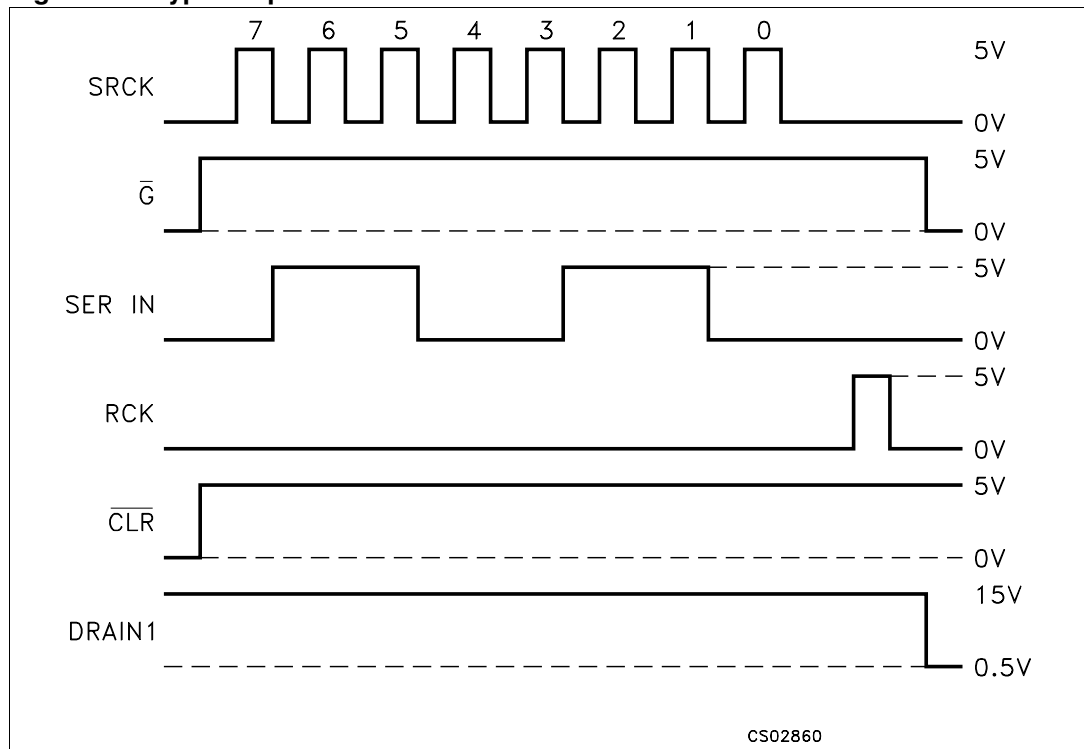


Figure 5. Typical operation mode waveforms



- Note: 1 A) The word generator has the following characteristics: $t_r \leq 10 \text{ ns}$, $t_f \leq 10 \text{ ns}$, $t_W = 300 \text{ ns}$, pulse repetition rate (PRR) = 5 kHz, $Z_O = 50 \Omega$
 2 B) C_L includes probe and jig capacitance.

Figure 6. Typical operation mode test circuits

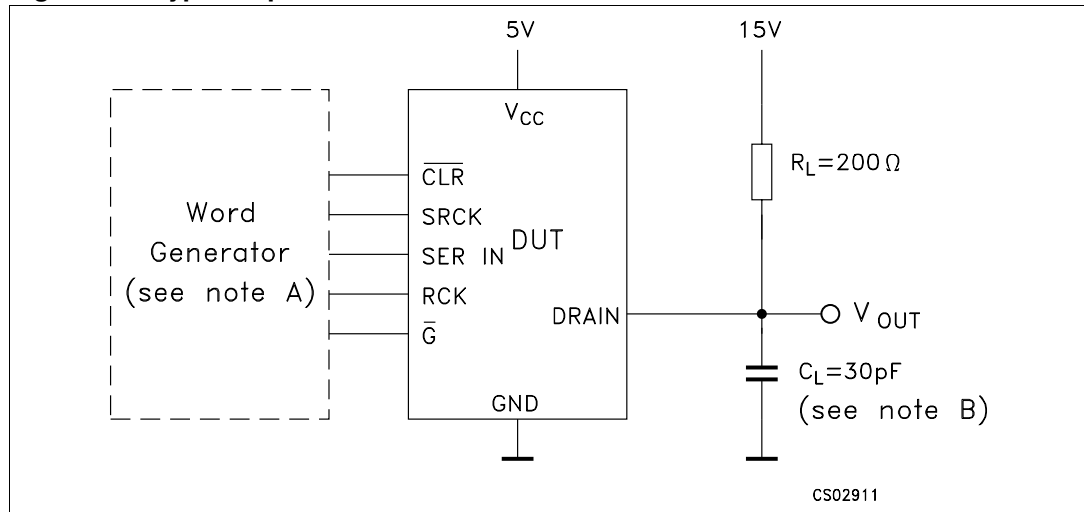


Figure 7. Switching time waveform

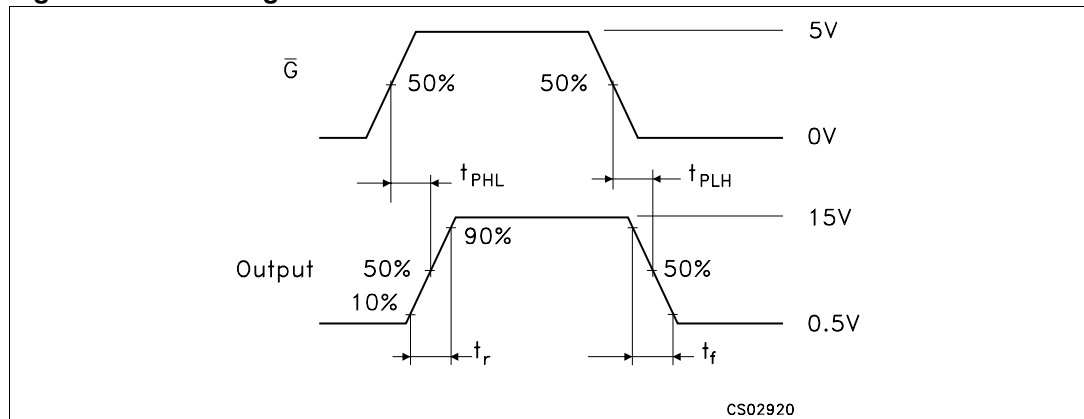
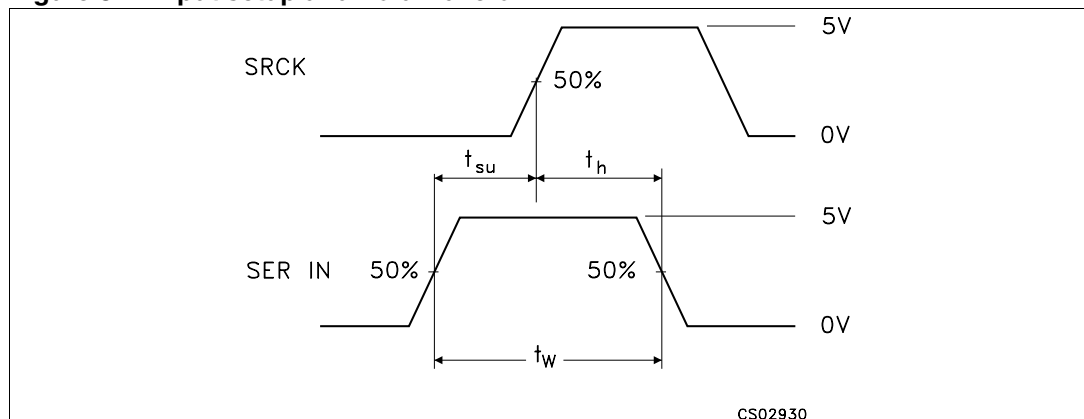


Figure 8. Input setup and hold waveform



- Note:
- 1 A) The word generator has the following characteristics: $t_r \leq 10 \text{ ns}$, $t_f \leq 10 \text{ ns}$, $t_W = 300 \text{ ns}$, pulse repetition rate (PRR) = 5 kHz, $Z_O = 50 \Omega$
 - 2 B) C_L includes probe and jig capacitance.

Figure 9. Reverse recovery current test circuits

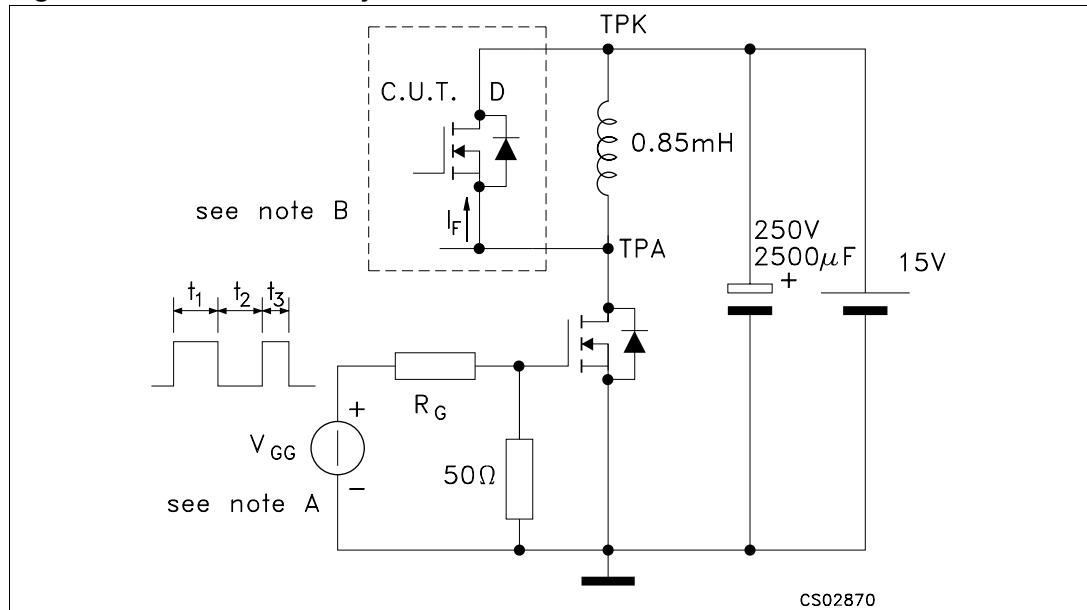
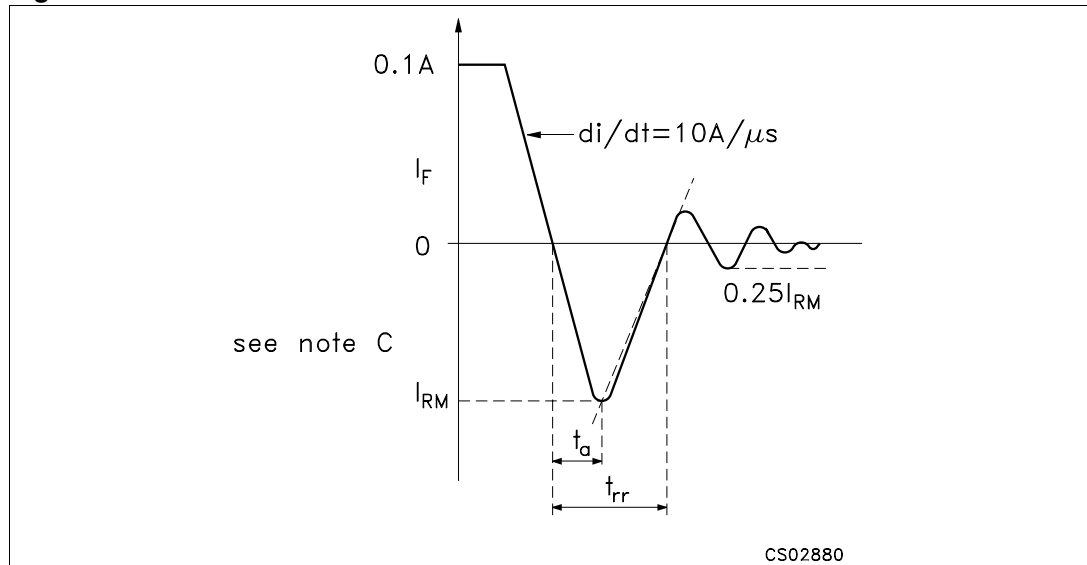


Figure 10. Source drain diode waveform



- Note:
- 1 A) The V_{GG} amplitude and R_G are adjusted for $di/dt = 10 A/\mu s$. A V_{GG} double-pulse train is used to set $I_F = 0.1 A$, where $t_1 = 10 \mu s$, $t_2 = 7 \mu s$ and $t_3 = 3 \mu s$
 - 2 B) The drain terminal under test is connected to the TPK test point. All other terminals are connected together and connected to the TPA test point.
 - 3 C) I_{RM} = maximum recovery current.

Figure 11. Single pulse avalanche energy test circuits

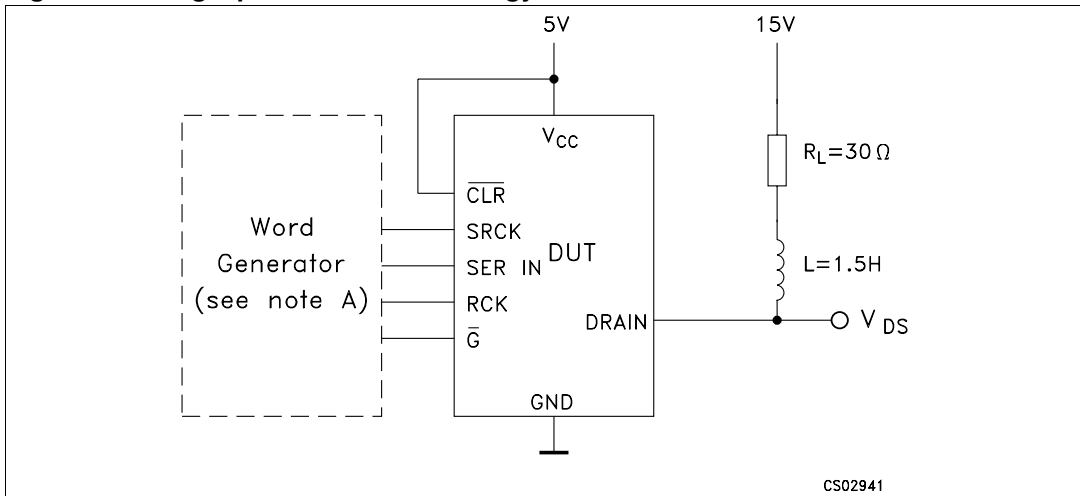
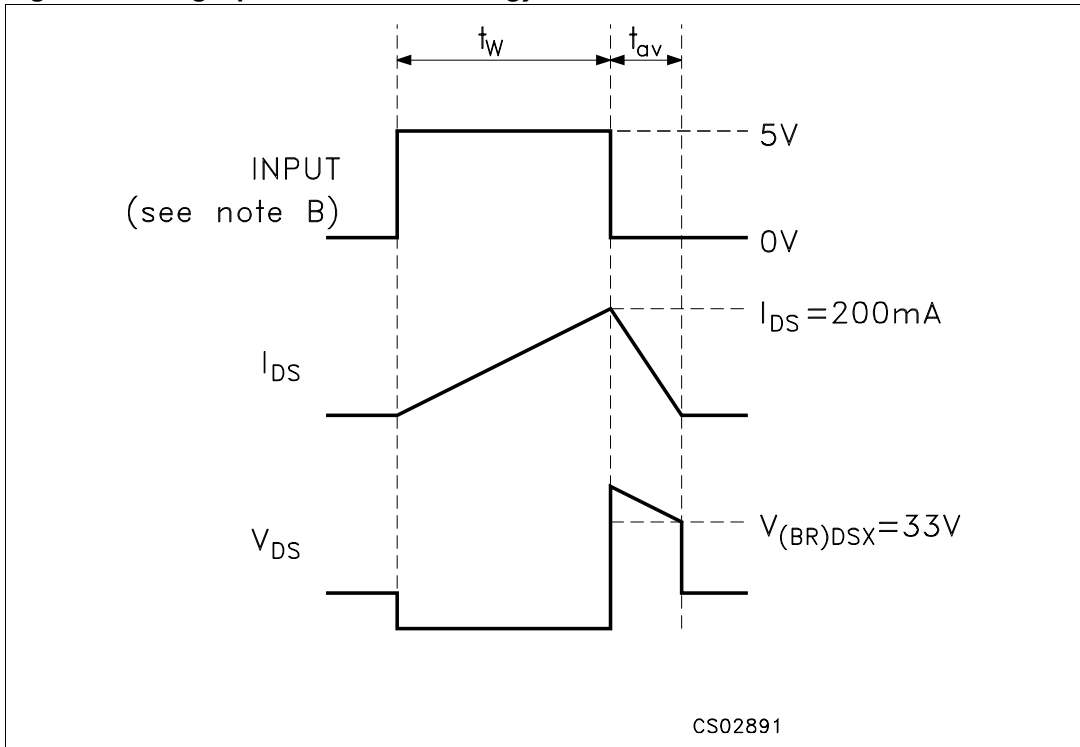


Figure 12. Single pulse avalanche energy waveform



- Note:
- 1 A) The word generator has the following characteristics: $t_r \leq 10 \text{ ns}$, $t_f \leq 10 \text{ ns}$, $Z_O = 50 \Omega$
 - 2 B) Input pulse duration, t_W is increased until peak current $I_{AS} = 200 \text{ mA}$. Energy test level is defined as $E_{AS} = (I_{AS} \times V_{(BR)DSX} \times t_{AV})/2 = 30 \text{ mJ}$.

6 Typical performance and characteristics

(unless otherwise specified $T_J = 25\text{ }^\circ\text{C}$)

Figure 13. Max continuous drain current vs number of outputs conducting simultaneously

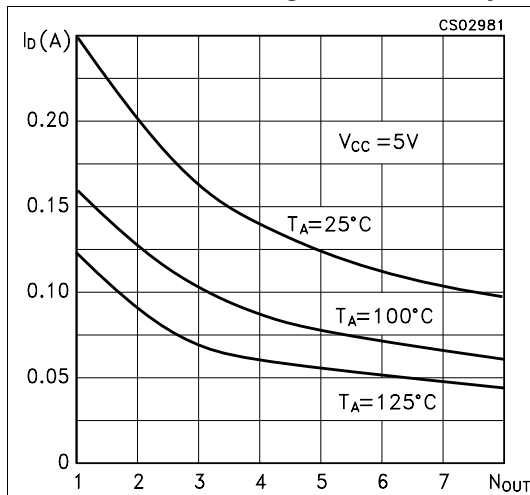


Figure 14. Static drain-source on-state resistance vs drain current

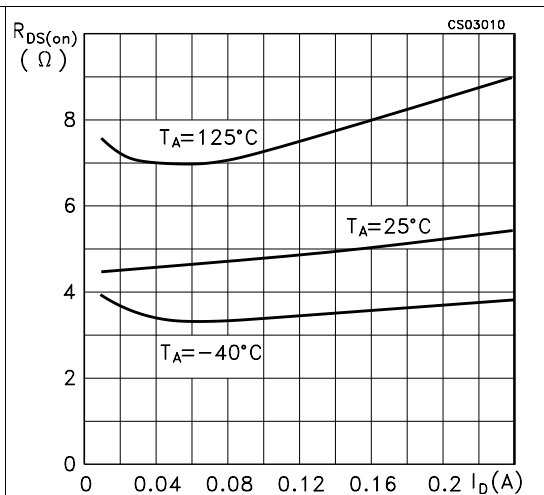


Figure 15. Maximum peak drain current vs number of outputs conducting simultaneously

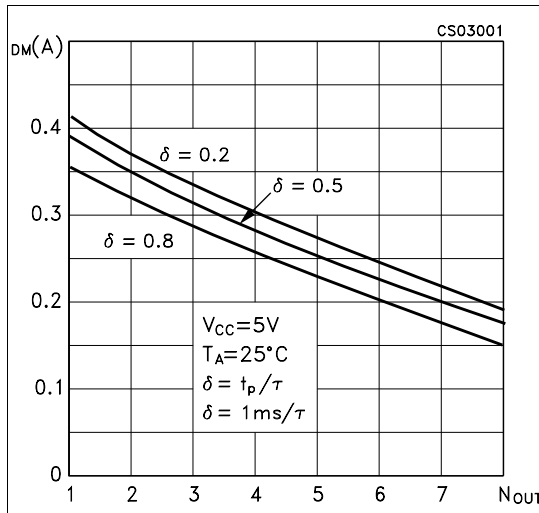


Figure 16. Static drain-source on-state resistance vs logic supply voltage

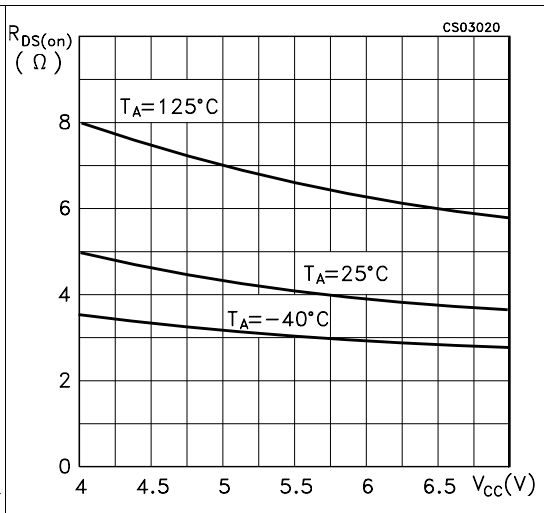


Figure 17. Peak avalanche current vs time duration of avalanche

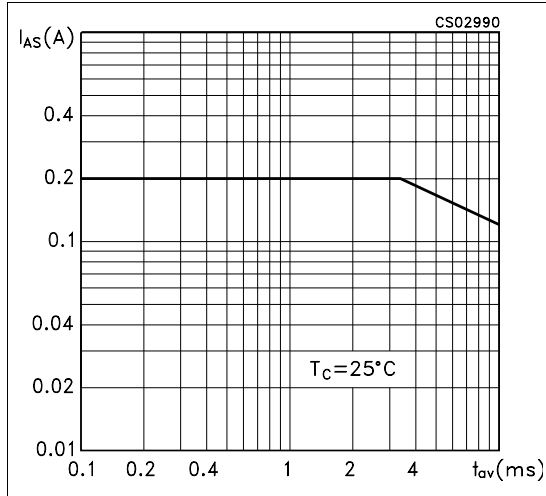


Figure 18. Supply current vs frequency

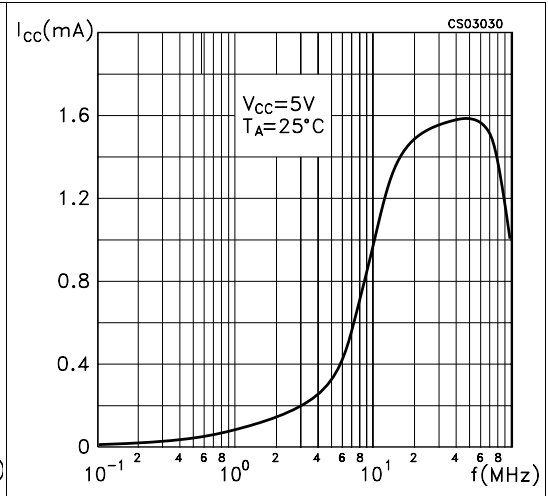


Figure 19. Supply current vs supply voltage

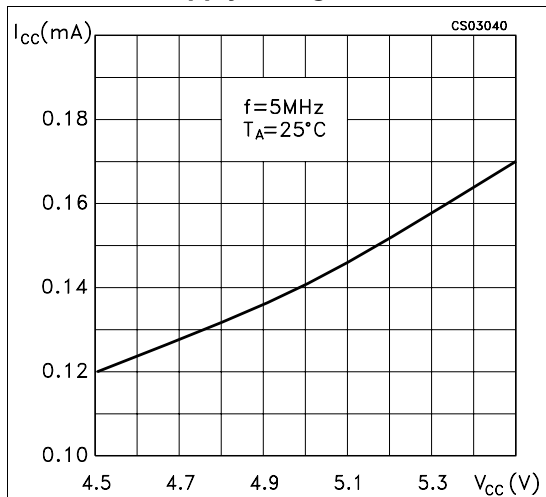


Figure 20. Switching time vs case temperature

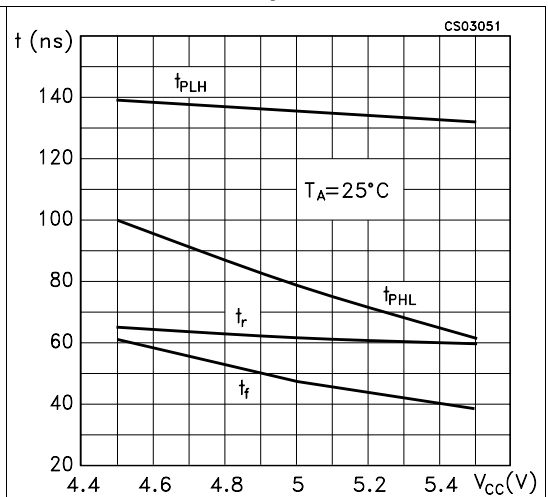
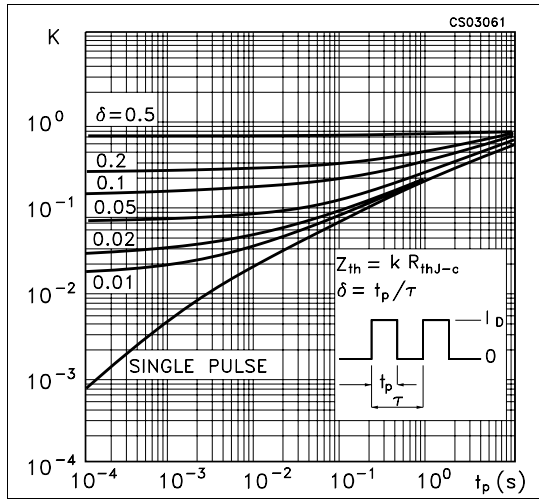


Figure 21. Normalized junction to ambient thermal resistance

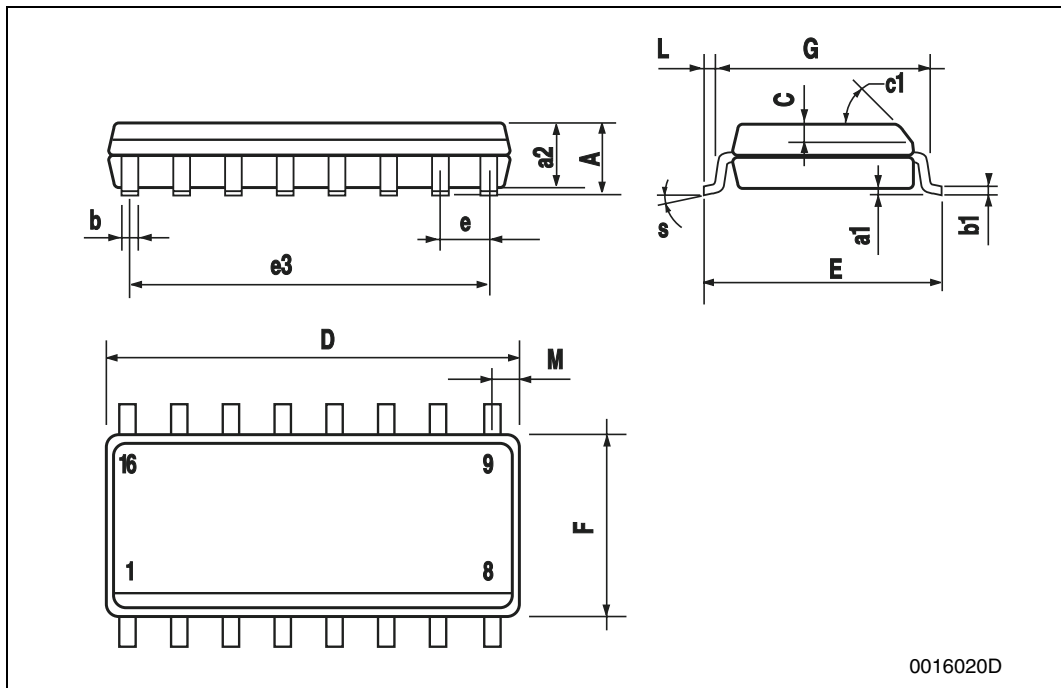


7 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

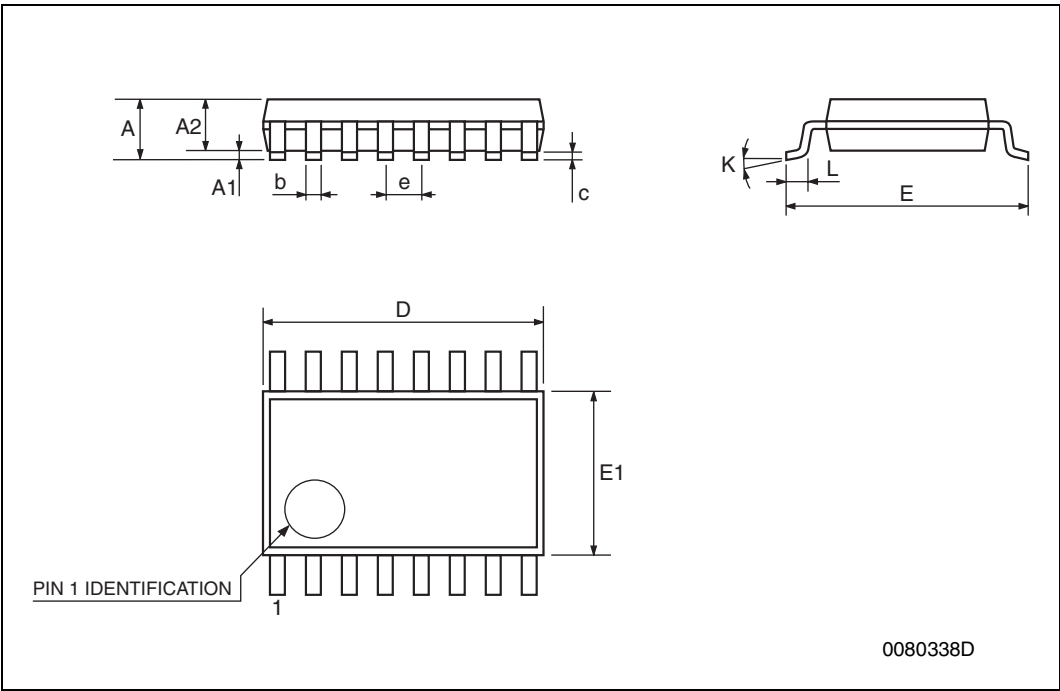
SO-16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.004		0.010
a2			1.64			0.063
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



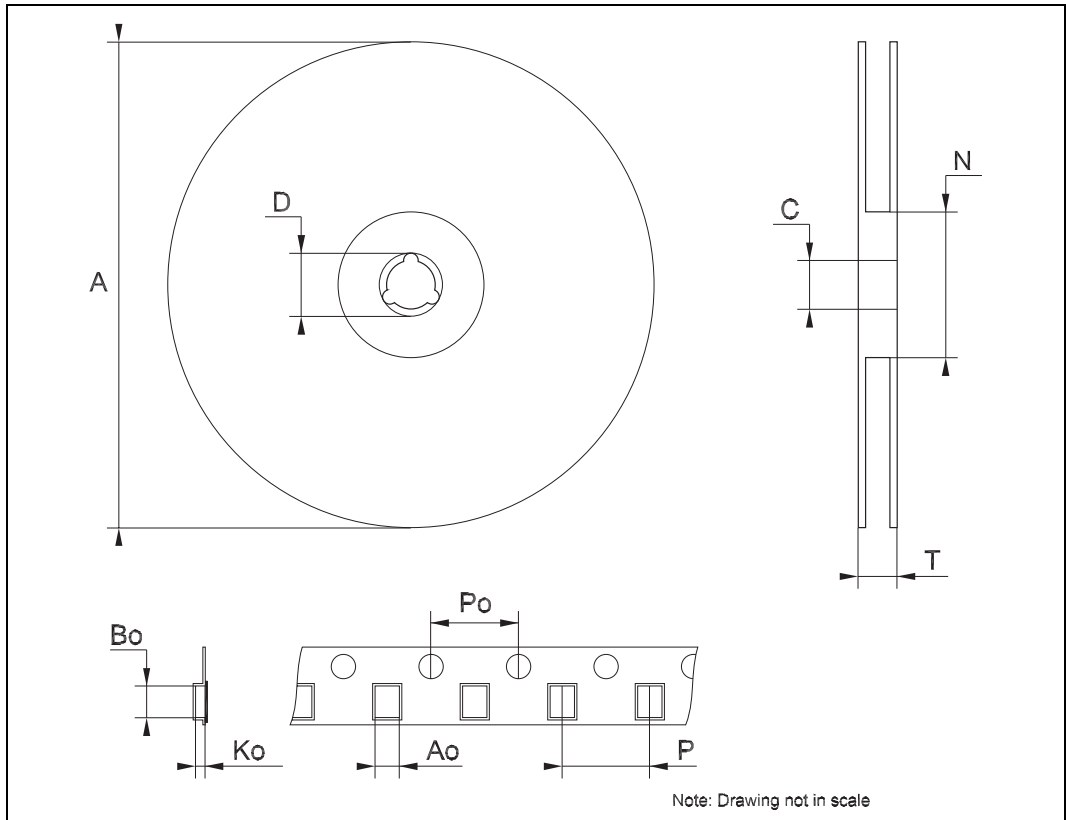
TSSOP16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0079
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



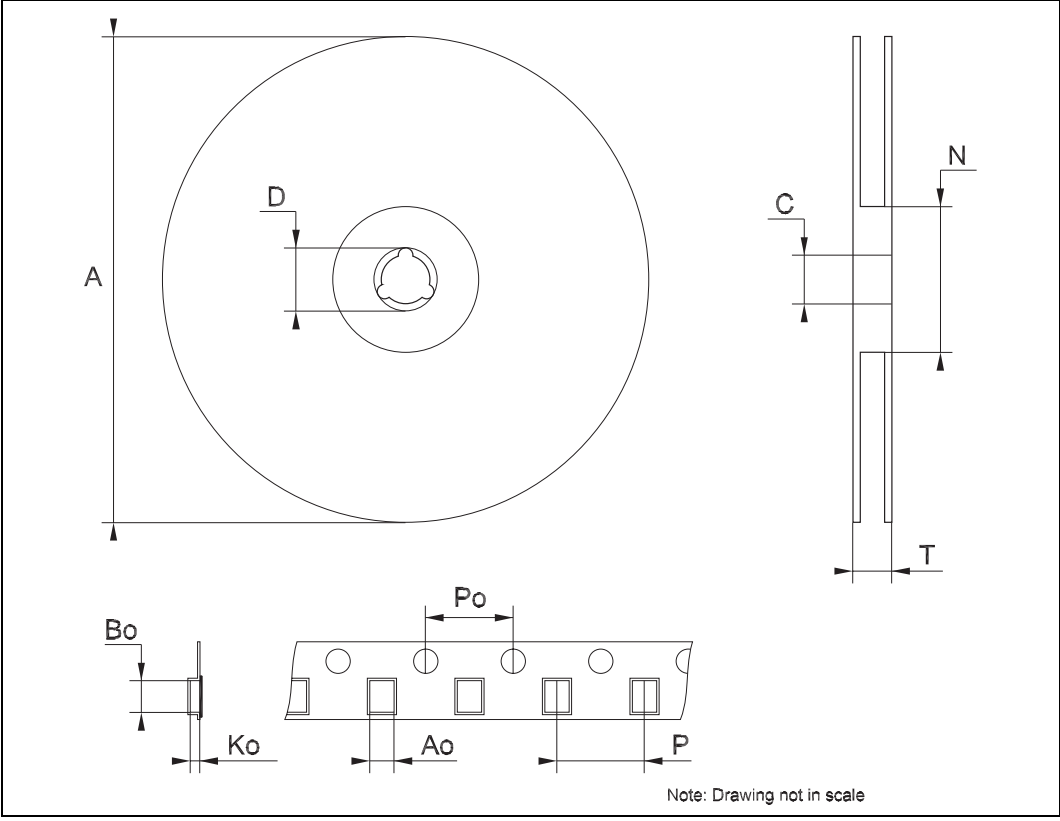
Tape & Reel SO-16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			22.4			0.882
Ao	6.45		6.65	0.254		0.262
Bo	10.3		10.5	0.406		0.414
Ko	2.1		2.3	0.082		0.090
Po	3.9		4.1	0.153		0.161
P	7.9		8.1	0.311		0.319



Tape & Reel TSSOP16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			22.4			0.882
Ao	6.7		6.9	0.264		0.272
Bo	5.3		5.5	0.209		0.217
Ko	1.6		1.8	0.063		0.071
Po	3.9		4.1	0.153		0.161
P	7.9		8.1	0.311		0.319



8 Revision history

Table 7. Document revision history

Date	Revision	Changes
07-Jul-2004	2	Update Figure 3
07-May-2007	3	Document reformatted, tube package deleted
21-May-2008	4	Update: tsu and ThL values in Table 4 , ESD value on cover page
16-Mar-2009	5	Updated Table 5 on page 6

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На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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